

## 产品规格书

### Specifcation of products

产品名称:可控硅模块

产品型号: MTC400A-Y04

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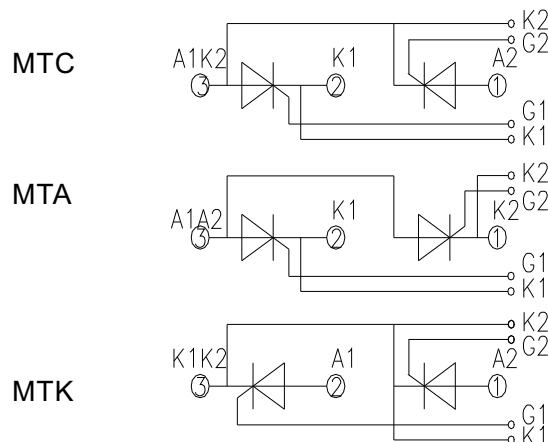
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| 拟制  | 审核  | 核准 |
| 林益龙 | 曹剑龙 | 宗瑞 |

| SYMBOL                               | CHARACTERISTIC                                                       | TEST CONDITIONS                                                                                                                             | T <sub>j</sub> (°C) | VALUE |      |       | UNIT                             |
|--------------------------------------|----------------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------|---------------------|-------|------|-------|----------------------------------|
|                                      |                                                                      |                                                                                                                                             |                     | Min   | Type | Max   |                                  |
| I <sub>T(AV)</sub>                   | Mean on-state current                                                | 180° half sine wave 50Hz<br>Single side cooled, T <sub>c</sub> =85°C                                                                        | 125                 |       |      | 400   | A                                |
| I <sub>T(RMS)</sub>                  | RMS on-state current                                                 | Single side cooled, T <sub>c</sub> =85°C                                                                                                    | 125                 |       |      | 628   | A                                |
| V <sub>DRM</sub><br>V <sub>RRM</sub> | Repetitive peak off-state voltage<br>Repetitive peak reverse voltage | V <sub>DRM</sub> &V <sub>RRM</sub> tp=10ms<br>V <sub>DSM</sub> &V <sub>RSM</sub> = V <sub>DRM</sub> &V <sub>RRM</sub> +200V<br>respectively | 125                 | 600   |      | 1800  | V                                |
| I <sub>DRM</sub><br>I <sub>RRM</sub> | Repetitive peak current                                              | at V <sub>DRM</sub><br>at V <sub>RRM</sub>                                                                                                  | 125                 |       |      | 40    | mA                               |
| I <sub>TSM</sub>                     | Surge on-state current                                               | 10ms half sine wave                                                                                                                         | 125                 |       |      | 12.0  | KA                               |
| I <sup>2</sup> t                     | I <sup>2</sup> T for fusing coordination                             | V <sub>R</sub> =60%V <sub>RRM</sub>                                                                                                         |                     |       |      | 734   | A <sup>2</sup> s*10 <sup>3</sup> |
| V <sub>TO</sub>                      | Threshold voltage                                                    |                                                                                                                                             | 125                 |       |      | 0.80  | V                                |
| r <sub>T</sub>                       | On-state slop resistance                                             |                                                                                                                                             |                     |       |      | 0.49  | mΩ                               |
| V <sub>TM</sub>                      | Peak on-state voltage                                                | I <sub>TM</sub> =1200A                                                                                                                      | 125                 |       |      | 1.5   | V                                |
| dv/dt                                | Critical rate of rise of off-state voltage                           | V <sub>DM</sub> =67%V <sub>DRM</sub>                                                                                                        | 125                 |       |      | 800   | V/μs                             |
| di/dt                                | Critical rate of rise of on-state current                            | From 67%V <sub>DRM</sub><br>to 1200A, Gate source 1.5A<br>t <sub>r</sub> ≤0.5μs Repetitive                                                  | 125                 |       |      | 150   | A/μs                             |
| I <sub>GT</sub>                      | Gate trigger current                                                 | V <sub>A</sub> =12V, I <sub>A</sub> =1A                                                                                                     | 25                  | 30    |      | 200   | mA                               |
| V <sub>GT</sub>                      | Gate trigger voltage                                                 |                                                                                                                                             |                     | 1.0   |      | 3.0   | V                                |
| I <sub>H</sub>                       | Holding current                                                      |                                                                                                                                             |                     | 20    |      | 100   | mA                               |
| V <sub>GD</sub>                      | Non-trigger gate voltage                                             | At 67%V <sub>DRM</sub>                                                                                                                      | 125                 |       |      | 0.2   | V                                |
| R <sub>th(j-c)</sub>                 | Thermal resistance<br>Junction to heatsink                           | At 180° sine Single side cooled                                                                                                             |                     |       |      | 0.080 | °C /W                            |
| V <sub>iso</sub>                     | Isolation voltage                                                    | 50Hz, RM. S, t=1min, I <sub>iso</sub> : 1mA (MAX)                                                                                           |                     | 2500  |      |       | V                                |
| F <sub>m</sub>                       | Thermal connection torque (M10)                                      |                                                                                                                                             |                     |       | 9.0  |       | N.m                              |
|                                      | Mounting torque (M6)                                                 |                                                                                                                                             |                     |       | 5.0  |       | N.m                              |
| T <sub>stg</sub>                     | Stored temperature                                                   |                                                                                                                                             |                     | -40   |      | 140   | °C                               |
| W <sub>t</sub>                       | Weight                                                               |                                                                                                                                             |                     |       | 1150 |       | g                                |
| Outline                              |                                                                      |                                                                                                                                             |                     |       |      |       |                                  |

### OUTLINE DRAWING & CIRCUIT DIAGRAM



### Rating and Characteristic

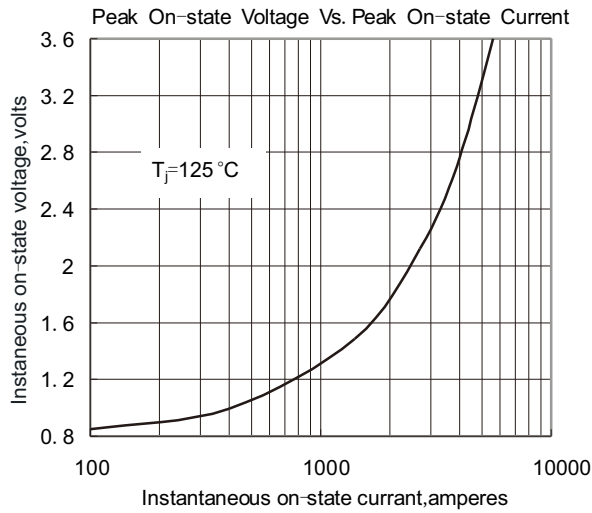


Fig. 1

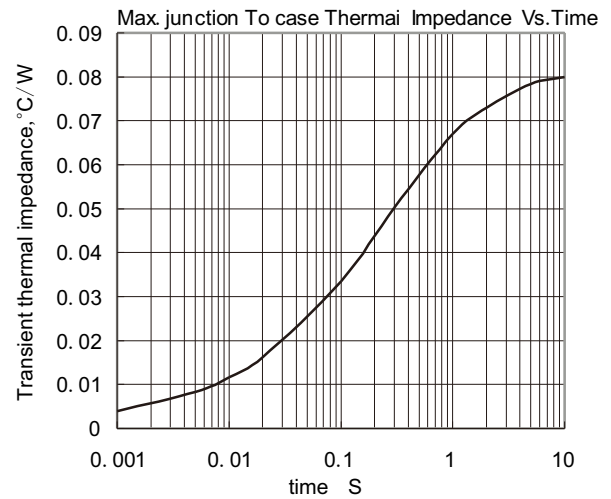


Fig. 2

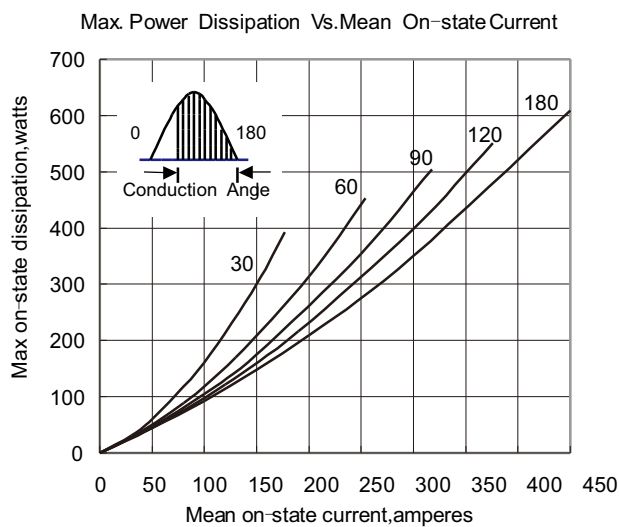


Fig. 3

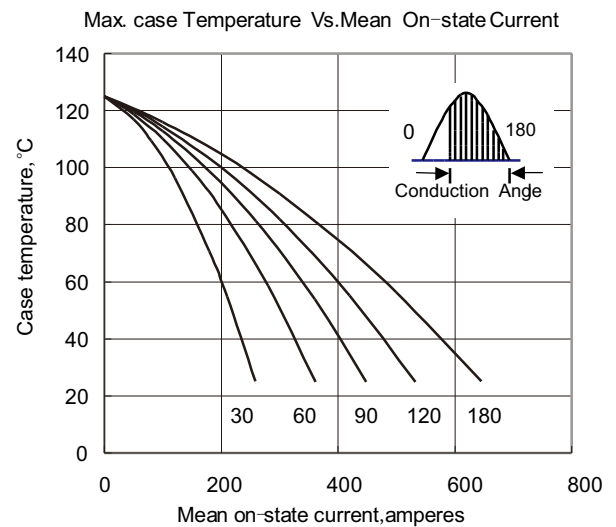


Fig. 4

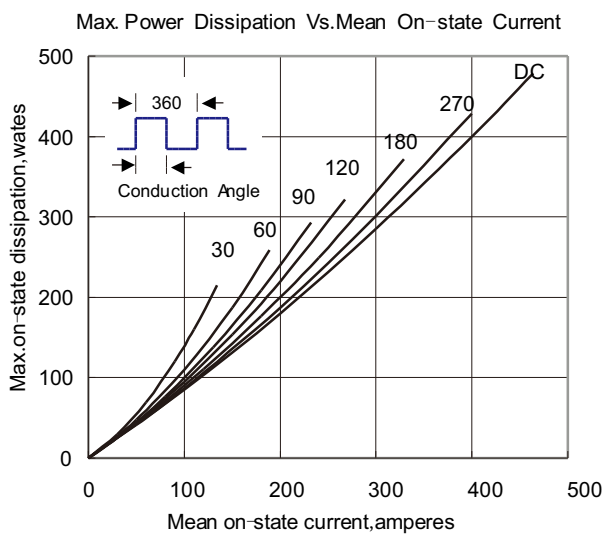


Fig. 5

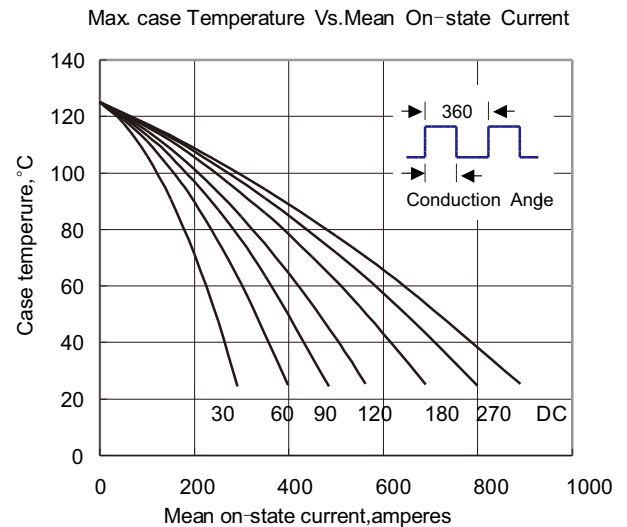


Fig. 6

## Rating and Characteristic

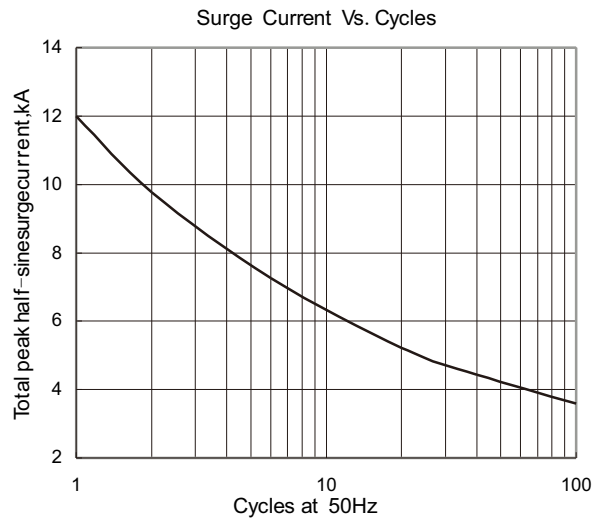


Fig. 7

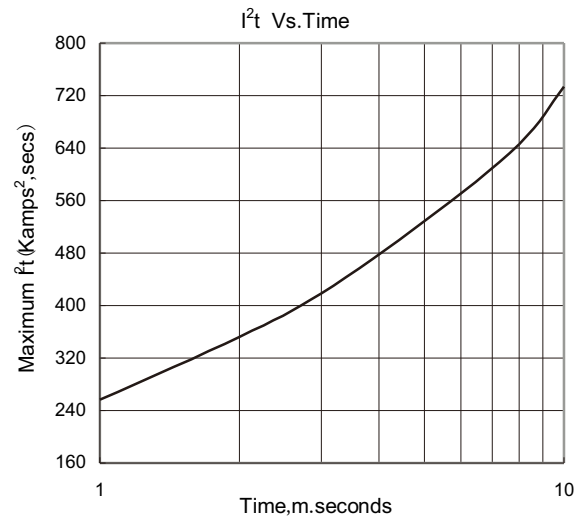


Fig. 8

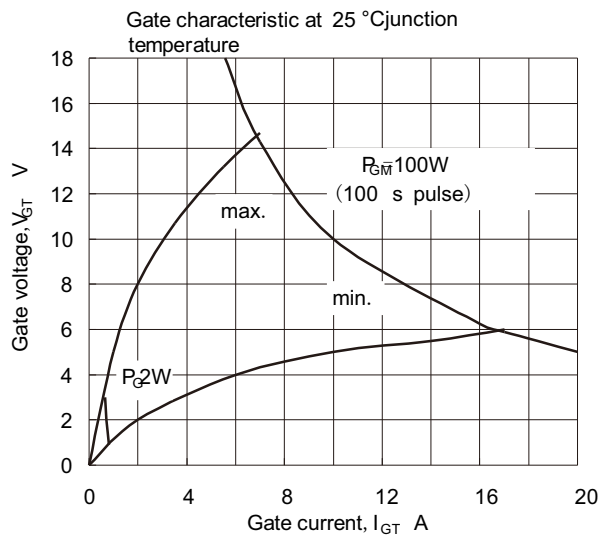


Fig. 9

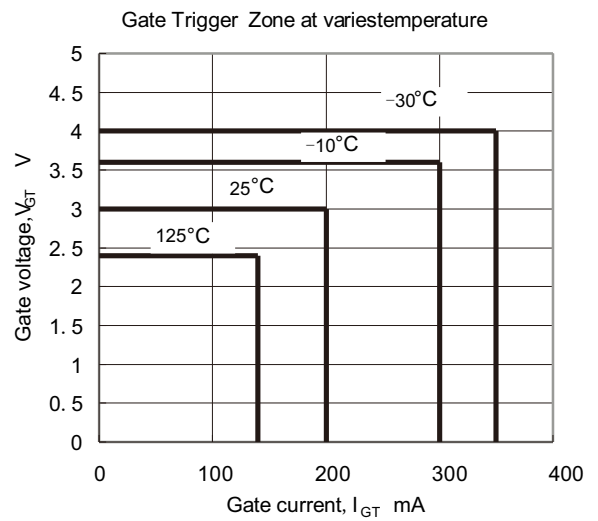


Fig. 10

## Outside Dimension

